Single, Dual, Quad Low-Voltage, Rail-to-Rail Operational Amplifiers

The LMV321, LMV358, and LMV324 are CMOS single, dual, and quad low voltage operational amplifiers with rail-to-rail output swing. These amplifiers are a cost-effective solution for applications where low power consumption and space saving packages are critical. Specification tables are provided for operation from power supply voltages at 2.7 V and 5 V. Rail-to-Rail operation provides improved signal-to-noise preformance. Ultra low quiescent current makes this series of amplifiers ideal for portable, battery operated equipment. The common mode input range includes ground making the device useful for low-side current-shunt measurements. The ultra small packages allow for placement on the PCB in close proximity to the signal source thereby reducing noise pickup.

Features

- Operation from 2.7 V to 5.0 V Single-Sided Power Supply
- LMV321 Single Available in Ultra Small 5 Pin SC70 Package
- No Output Crossover Distortion
- Industrial temperature Range: -40°C to +85°C
- Rail-to-Rail Output
- Low Quiescent Current: LMV358 Dual 220 μA, Max per Channel
- No Output Phase–Reversal from Overdriven Input
- These are Pb-Free Devices

Typical Applications

- Notebook Computers and PDA's
- Portable Battery-Operated Instruments
- Active Filters

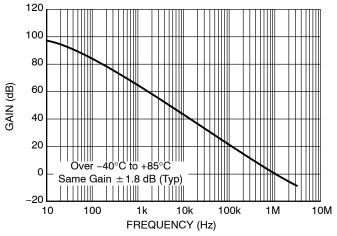


Figure 1. Open Loop Frequency Response $(R_L = 2 \text{ k}\Omega, T_A = 25^{\circ}\text{C}, V_S = 5 \text{ V})$

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.



ON Semiconductor®

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SOIC-8 CASE 751







SOIC-14 CASE 751A

TSSOP-14 CASE 948G

ORDERING AND MARKING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

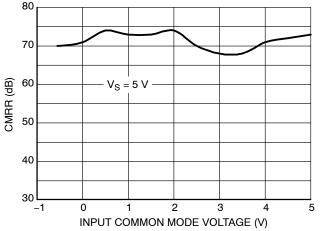
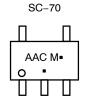


Figure 2. CMRR vs. Input Common Mode Voltage

MARKING DIAGRAMS



AAC = Specific Device Code

Μ = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

TSOP-5



3AC = Specific Device Code

= Assembly Location

= Year = Work Week W = Pb-Free Package

Micro8 8 AAAA V358 AYW= 1 **| | | | | | | |**

V358 = Specific Device Code = Assembly Location Α

Υ = Year = Work Week W

= Pb-Free Package

(Note: Microdot may be in either location) (Note: Microdot may be in either location)



V358 = Specific Device Code = Assembly Location Α

L = Wafer Lot Υ = Year W = Work Week

= Pb-Free Package

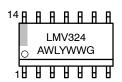
AC M

AC = Specific Device Code

UDFN8

= Date Code Μ

= Pb-Free Package



SOIC-14

LMV324 = Specific Device Code

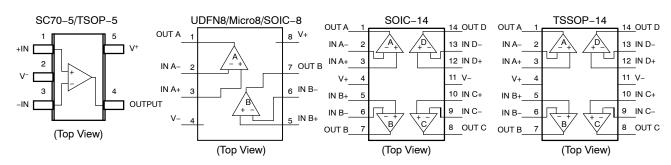
= Assembly Location WL= Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package



LMV324 = Specific Device Code = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

PIN CONNECTIONS



MAXIMUM RATINGS

Symbol	Rating	Value	Unit
Vs	Supply Voltage (Operating Range V _S = 2.7 V to 5.5 V)	5.5	V
V _{IDR}	Input Differential Voltage	± Supply Voltage	V
V _{ICR}	Input Common Mode Voltage Range	-0.5 to (V+) + 0.5	V
	Maximum Input Current	10	mA
t _{So}	Output Short Circuit (Note 1)	Continuous	
TJ	Maximum Junction Temperature	150	°C
T _A	Operating Ambient Temperature Range LMV321, LMV358, LMV324 NCV321 (Note 2)	-40°C to 85°C -40°C to 125°C	°C °C
$\theta_{\sf JA}$	Thermal Resistance:		°C/W
	SC-70	280	
	Micro8	238	
	TSOP-5	333	
	UDFN8 (1.2 mm x 1.8 mm x 0.5 mm)	350	
	SOIC-8	212	
	SOIC-14	156	
	TSSOP-14	190	
T _{stg}	Storage Temperature	-65 to 150	°C
	Mounting Temperature (Infrared or Convection –20 sec)	260	°C
V _{ESD}	ESD Tolerance (Note 3) LMV321, NCV321 Machine Model Human Body Model LMV358/324 Machine Model Human Body Model	100 1000 100 2000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Continuous short-circuit operation to ground at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of 45 mA over long term may adversely affect reliability. Shorting output to either V+ or V- will adversely affect reliability.

^{2.} NCV prefix is qualified for automotive usage.

Human Body Model, applicable std. MIL-STD-883, Method 3015.7
 Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC)
 Field-Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).

2.7 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V^+ = 2.7$ V, $R_L = 1 M\Omega$, $V^- = 0 V$, $V_O = V+/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	$T_A = T_{Low}$ to T_{High} (Note 4)		1.7	9	mV
Input Offset Voltage Average Drift	ICV _{OS}	$T_A = T_{Low}$ to T_{High} (Note 4)		5		μV/°C
Input Bias Current	I _B	$T_A = T_{Low}$ to T_{High} (Note 4)		<1		nA
Input Offset Current	I _{IO}	$T_A = T_{Low}$ to T_{High} (Note 4)		<1		nA
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \le \text{V}_{\text{CM}} \le 1.7 \text{ V}$	50	63		dB
Power Supply Rejection Ratio	PSRR	$2.7 \text{ V} \le \text{V+} \le 5 \text{ V},$ $\text{V}_0 = 1 \text{ V}$	50	60		dB
Input Common-Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 1.7	-0.2 to 1.9		V
Output Swing	V _{OH}	R_L = 10 kΩ to 1.35 V	V _{CC} – 100	V _{CC} – 10		mV
	V _{OL}	R_L = 10 k Ω to 1.35 V (Note 5)		60	180	mV
Supply Current LMV321 LMV358 (Both Amplifiers) LMV324 (4 Amplifiers)	I _{CC}			80 140 260	185 340 680	μΑ

2.7 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V^+ = 2.7$ V, R_L = 1 $M\Omega,\,V^-$ = 0 V, V_O = V+/2)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		٥
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√ Hz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product For LMV321, LMV358, LMV324: T_A = -40°C to +85°C
 Guaranteed by design and/or characterization.

5.0 V DC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25^{\circ}C$, $V^+ = 5.0$ V, $R_L = 1 M\Omega$, $V^- = 0 V$, $V_O = V+/2$)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Input Offset Voltage	V _{IO}	T _A = T _{Low} to T _{High} (Note 6)		1.7	9	mV
Input Offset Voltage Average Drift	T_CV_{IO}	T _A = T _{Low} to T _{High} (Note 6)		5		μV/°C
Input Bias Current (Note 7)	Ι _Β	T _A = T _{Low} to T _{High} (Note 6)		< 1		nA
Input Offset Current (Note 7)	I _{IO}	$T_A = T_{Low}$ to T_{High} (Note 6)		< 1		nA
Common Mode Rejection Ratio	CMRR	$0 \text{ V} \leq \text{V}_{\text{CM}} \leq 4 \text{ V}$	50	65		dB
Power Supply Rejection Ratio	PSRR	$2.7 \text{ V} \le \text{V+} \le 5 \text{ V},$ $\text{V}_{\text{O}} = 1 \text{ V}, \text{V}_{\text{CM}} = 1 \text{ V}$	50	60		dB
Input Common-Mode Voltage Range	V _{CM}	For CMRR ≥ 50 dB	0 to 4	-0.2 to 4.2		V
Large Signal Voltage Gain (Note 7)	A _V	$R_L = 2 k\Omega$	15	100		V/mV
		T _A = T _{Low} to T _{High} (Note 6)	10			
Output Swing	V _{OH}	$R_L = 2 k\Omega$ to 2.5 V $T_A = T_{Low}$ to T_{High} (Note 6)	V _{CC} - 300 V _{CC} - 400	V _{CC} - 40		mV
	V _{OL}	$R_L = 2 \text{ k}\Omega$ to 2.5 V (Note 7) $T_A = T_{Low}$ to T_{High} (Note 6)		120	300 400	mV
	V _{OH}	R_L = 10 k Ω to 2.5 V (Note 7) T_A = T_{Low} to T_{High} (Note 6)	V _{CC} - 100 V _{CC} - 200			mV
	V _{OL}	R_L = 10 k Ω to 2.5 V T_A = T_{Low} to T_{High} (Note 6)		65	180 280	mV
Output Short Circuit Current	Io	Sourcing = V _O = 0 V (Note 7) Sinking = V _O = 5 V (Note 7)	10 10	60 160		mA
Supply Current	Icc	LMV321 $T_A = T_{Low}$ to T_{High} (Note 6)		130	250 350	μΑ
		NCV321 T _A = T _{Low} to T _{High} (Note 6)		130	250 350	
		LMV358 Both Amplifiers $T_A = T_{Low}$ to T_{High} (Note 6)		210	440 615	
		LMV324 All Four Amplifiers $T_A = T_{Low}$ to T_{High} (Note 6)		410	830 1160	

5.0 V AC ELECTRICAL CHARACTERISTICS (Unless otherwise specified, all limits are guaranteed for $T_A = 25$ °C, $V^+ = 5.0$ V, $R_L=1~M\Omega,~V^-=0~V,~V_O=V+/2)$

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Slew Rate	S _R			1		V/μs
Gain Bandwidth Product	GBWP	C _L = 200 pF		1		MHz
Phase Margin	Θ_{m}			60		٥
Gain Margin	G _m			10		dB
Input-Referred Voltage Noise	e _n	f = 50 kHz		50		nV/√ Hz

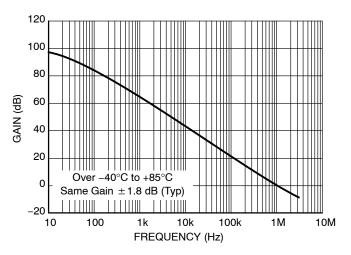
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. For LMV321, LMV358, LMV324: T_A = -40°C to +85°C
For NCV321: T_A = -40°C to +125°C.

7. Guaranteed by design and/or characterization.

TYPICAL CHARACTERISTICS

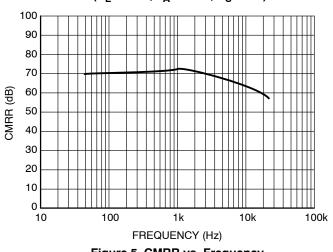
 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



170 150 130 PHASE MARGIN (°) 110 90 70 50 30 10 100 10k 100k 10M 10 1M FREQUENCY (Hz)

Figure 3. Open Loop Frequency Response (R_L = 2 k Ω , T_A = 25°C, V_S = 5 V)

Figure 4. Open Loop Phase Margin (R_L = 2 k Ω , T_A = 25°C, V_S = 5 V)



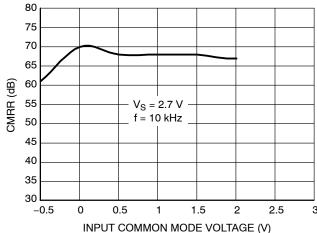
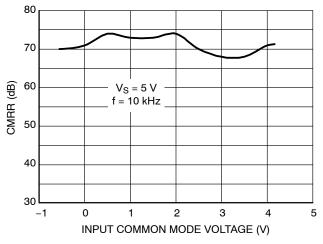


Figure 5. CMRR vs. Frequency (R_L = 5 k Ω , V_S = 5 V)

Figure 6. CMRR vs. Input Common Mode Voltage



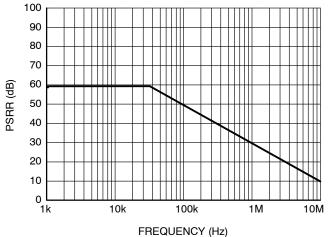
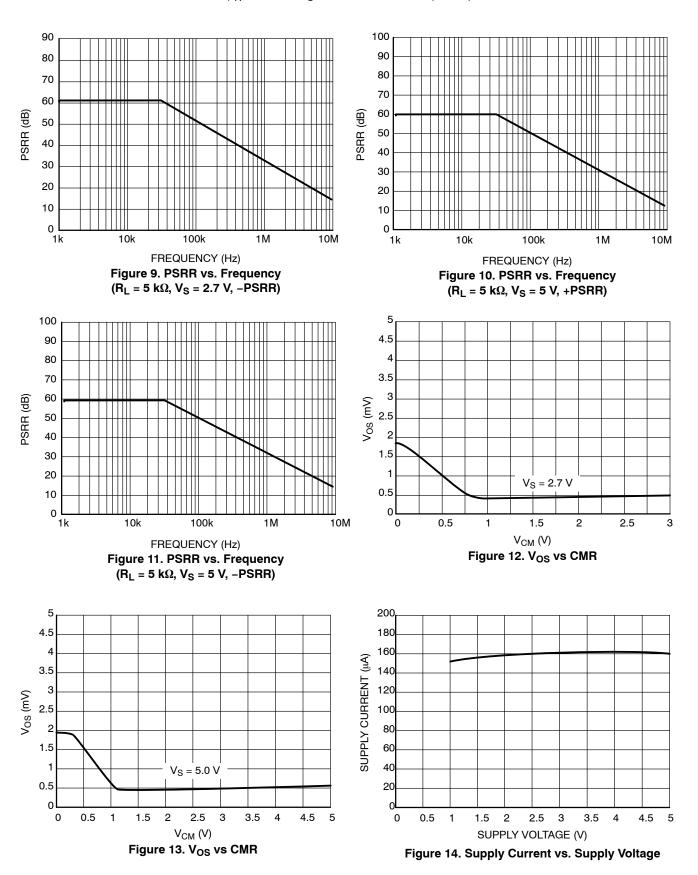


Figure 7. CMRR vs. Input Common Mode Voltage

Figure 8. PSRR vs. Frequency $(R_L = 5 k\Omega, V_S = 2.7 V, +PSRR)$

TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$



TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$

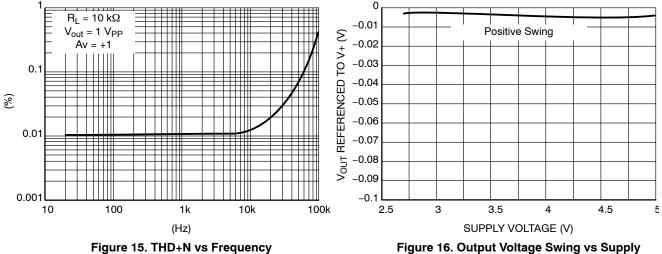


Figure 15. THD+N vs Frequency

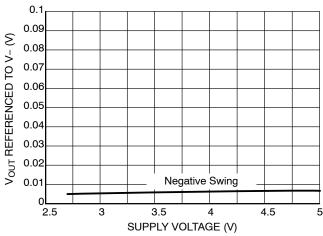


Figure 17. Output Voltage Swing vs Supply Voltage (R_L = 10k)

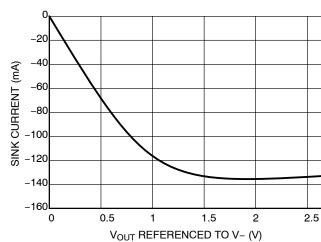


Figure 18. Sink Current vs. Output Voltage $V_S = 2.7 V$

Voltage (R_L = 10k)

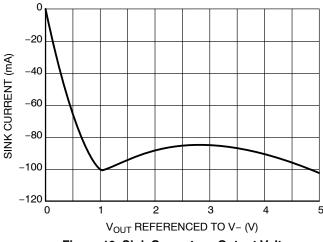


Figure 19. Sink Current vs. Output Voltage $V_S = 5.0 V$

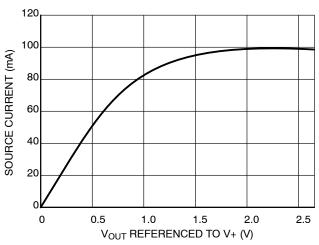


Figure 20. Source Current vs. Output Voltage $V_{S} = 2.7 V$

TYPICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ and } V_S = 5 \text{ V unless otherwise specified})$

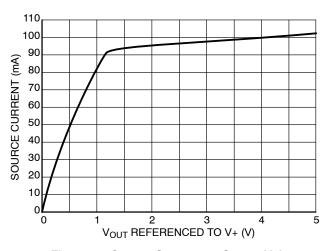


Figure 21. Source Current vs. Output Voltage $V_S = 5.0 \text{ V}$

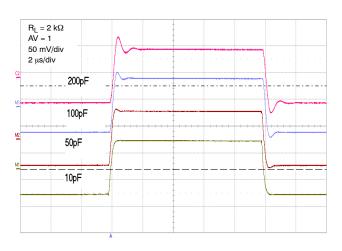


Figure 22. Settling Time vs. Capacitive Load

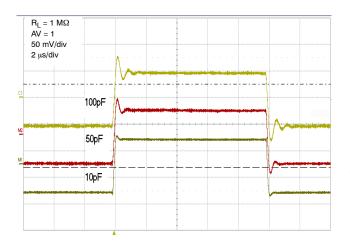


Figure 23. Settling Time vs. Capacitive Load

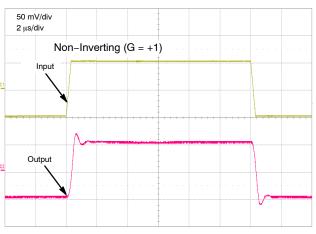


Figure 24. Step Response - Small Signal

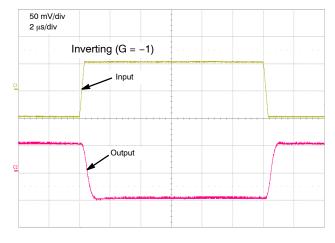


Figure 25. Step Response - Small Signal

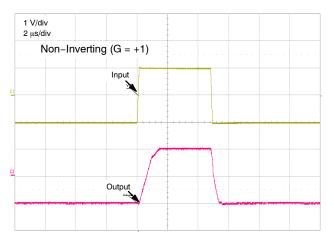


Figure 26. Step Response - Large Signal

TYPICAL CHARACTERISTICS

($T_A = 25^{\circ}C$ and $V_S = 5 V$ unless otherwise specified)

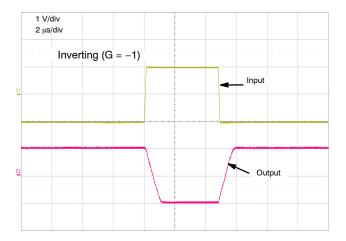


Figure 27. Step Response – Large Signal

APPLICATIONS

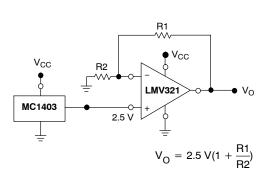


Figure 28. Voltage Reference

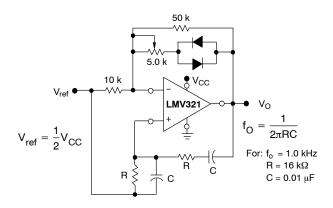


Figure 29. Wien Bridge Oscillator

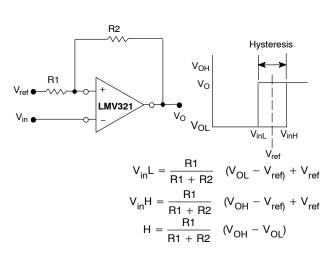
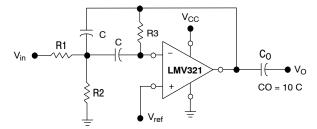


Figure 30. Comparator with Hysteresis



Given: f_0 = center frequency $A(f_0)$ = gain at center frequency

Choose value
$$f_o$$
, C
Then: $R3 = \frac{Q}{\pi f_O C}$

$$R1 = \frac{R3}{2 \, A(f_O)}$$

$$R2 = \frac{R1 \, R3}{4Q^2 \, R1 \, - \, R3}$$

For less than 10% error from operational amplifier, (($Q_O f_O$)/BW) < 0.1 where f_o and BW are expressed in Hz. If source impedance varies, filter may be preceded with voltage follower buffer to stabilize filter parameters.

Figure 31. Multiple Feedback Bandpass Filter

ORDERING INFORMATION

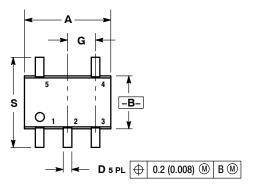
	Number of			
Order Number	Channels	Specific Device Marking	Package Type	Shipping [†]
LMV321SQ3T2G	Single	AAC	SC-70 (Pb-Free)	3000 / Tape & Reel
LMV321SN3T1G	Single	заС	TSOP-5 (Pb-Free)	3000 / Tape & Reel
NCV321SN3T1G* (In Development)	Single	заС	TSOP-5 (Pb-Free)	3000 / Tape & Reel
LMV358DMR2G	Dual	V358	Micro8 (Pb-Free)	4000 / Tape & Reel
LMV358MUTAG	Dual	AC	UDFN8 (Pb-Free)	3000 / Tape & Reel
LMV358DR2G	Dual	V358	SOIC-8 (Pb-Free)	2500 / Tape & Reel
LMV324DR2G	Quad	LMV324	SOIC-14 (Pb-Free)	2500 / Tape & Reel
LMV324DTBR2G	Quad	LMV 324	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

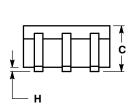
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

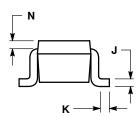
Capable.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE L



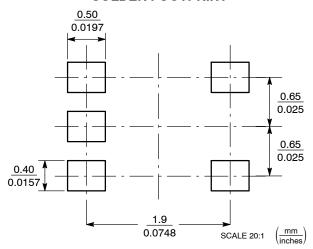




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

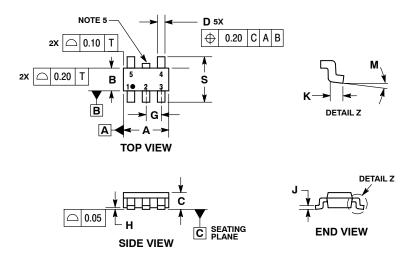
	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

SOLDER FOOTPRINT



PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE M



NOTES:

- VIES.

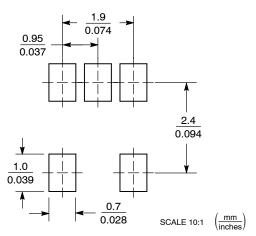
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

- 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.85	3.15		
В	1.35	1.65		
С	0.90	1.10		
D	0.25	0.50		
G	0.95	BSC		
Н	0.01	0.10		
J	0.10	0.26		
K	0.20	0.60		
М	0 °	10 °		
S	2.50	3.00		

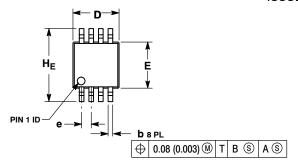
SOLDERING FOOTPRINT*

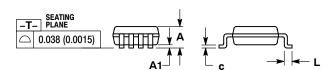


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

Micro8 CASE 846A-02 **ISSUE J**





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

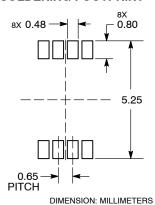
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. 846A-01 OBSOLETE, NEW STANDARD 846A-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	-		1.10			0.043
A1	0.05	0.08	0.15	0.002	0.003	0.006
b	0.25	0.33	0.40	0.010	0.013	0.016
С	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
E	2.90	3.00	3.10	0.114	0.118	0.122
е		0.65 BSC			0.026 BSC)
L	0.40	0.55	0.70	0.016	0.021	0.028
HE	4.75	4.90	5.05	0.187	0.193	0.199

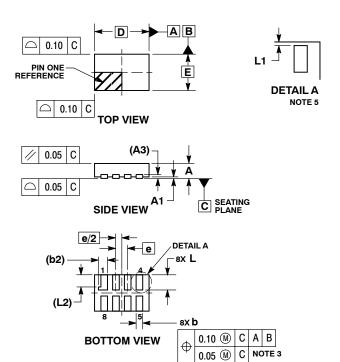
RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

UDFN8 1.8x1.2, 0.4P CASE 517AJ ISSUE O



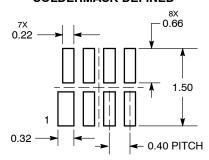
NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL TIP.
 4. MOLD FLASH ALLOWED ON TERMINALS ALONG EDGE OF PACKAGE. FLASH MAY NOT EXCEED 0.03 ONTO BOTTOM SURFACE OF TERMINALS.
 5. DETAIL A SHOWS OPTIONAL CONSTRUCTION FOR TERMINALS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
А3	0.127	REF	
b	0.15	0.25	
b2	0.30	REF	
D	1.80	BSC	
Е	1.20	BSC	
е	0.40	BSC	
L	0.45	0.55	
L1	0.00 0.03		
12	0.40	RFF	

MOUNTING FOOTPRINT* SOLDERMASK DEFINED

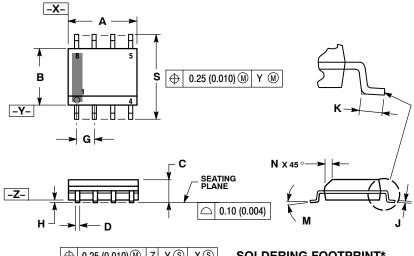


DIMENSIONS: MILLIMETERS

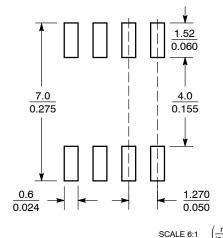
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOIC-8 NB CASE 751-07 **ISSUE AK**



⊕ 0.25 (0.010) M Z Y S XS **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

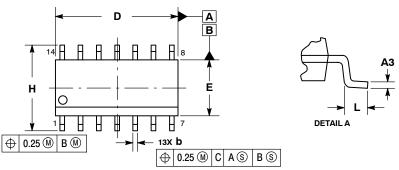
NOTES:

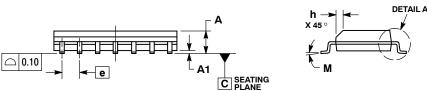
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 751.01 TURLULIZE1 OR ADEC DROUGTE. NEW
- 751–01 THRU 751–06 ARE OBSOLETE. NEW STANDARD IS 751–07.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
Ν	0.25	0.50	0.010	0.020	
s	5.80	6.20	0.228	0.244	

PACKAGE DIMENSIONS

SOIC-14 NB CASE 751A-03 **ISSUE L**





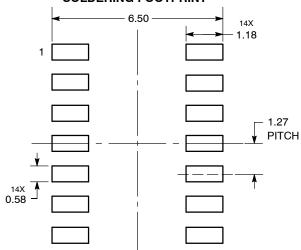
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b DOES NOT INCLUDE DAMBAR
- 3. DIMENSION & DOES NOT INCLUDE DAMBA PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.

 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIN	IETERS	ERS INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

SOLDERING FOOTPRINT*

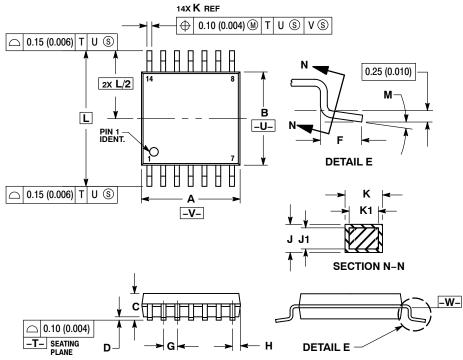


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G **ISSUE C**



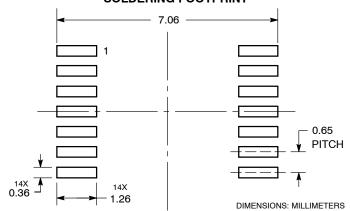
NOTES:

- DIMENSIONING AND TOLERANCING PER

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.03) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Г	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*



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